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Patent
Attorney's Docket No. 015290-502

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Helen H. ZHU et al.) Group Art Unit: Not Yet Assigned
Application No.: 09/820,694) Examiner: Not Yet Assigned
Filed: March 30, 2001)
For: METHOD OF PLASMA ETCHING)
SILICON NITRIDE)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please replace the first full paragraph beginning on line 8 of Page 8 with the following:

A1
The plasma for carrying out the silicon nitride etch can be produced in various types of plasma reactors. Such plasma reactors typically have energy sources which use RF energy, microwave energy, magnetic fields, etc. to produce a medium to high density plasma. For instance, a high density plasma could be produced in a transformer coupled plasma (TCP™) available from Lam Research Corporation which is also called inductively coupled plasma reactor, an electron-cyclotron resonance (ECR) plasma reactor, a helicon plasma reactor, or the like. An example of a high flow plasma reactor which can provide a high density plasma is disclosed in commonly owned U.S. Patent No. 5,820,723, the disclosure of which is hereby